

# **Evolution of carrier lifetime characteristics in Si structures during and post-irradiated by neutrons and protons**

*Monday 3 June 2013 10:40 (20 minutes)*

Motivation: to predict signal changes and to foresee possible modifications of the detector performance  
Comparison of variations of carrier drift and recombination characteristics during neutron and proton irradiations *in situ* and afterwards.

Comparative analysis of evolution of the carrier recombination characteristics

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